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“A process for producing thin layers in electronic devices such as integrated circuit chips, is provided. The process includes the steps of injecting a precursor fluid into a thermal processing chamber containing a substrate, such as a semiconductor wafer. The precursor fluid is converted into a solid which forms a layer on the substrate. In accordance with the present invention, the precursor fluid is pulsed into the process chamber in a manner such that the fluid is complet[ed]ly exhausted or removed from the chamber in between each pulse. Light energy can be used in forming the solid layers.”

IN THE CLAIMS

Please cancel claims 1-19, and 26-28, and 31-49.

Please amend claim 20 as follows (a copy of claim 20 showing insertions and deletions is attached as Appendix A):

20. A process for forming layers in electronic devices comprising the steps of:  
providing a reaction chamber;  
placing a semiconductor wafer in said reaction chamber;  
heating said semiconductor wafer with a thermal heating device placed adjacent to said wafer;  
pulsing a precursor fluid into said reaction chamber, said precursor fluid forming a solid layer on said semiconductor wafer;  
thereafter exposing said solid layer to light energy in said reaction chamber; and  
wherein between each pulse of said precursor fluid, (i) said reaction chamber is purged by flowing an inert gas through said reaction chamber in order to substantially remove any said precursor fluid not converted into a solid, and (ii) said solid layer is exposed to said light energy.

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